

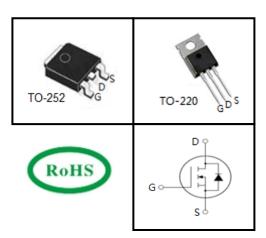
30V N-Channel Trench MOSFET

FEATURES

- Trench Power MOSFET Technology
- Low R_{DS(ON)}
- Low Gate Charge
- Optimized For Fast-switching Applications

APPLICATIONS

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial



Device Marking and Package Information		
Device	Package	Marking
TTD160N03GT	TO-252	160N03GT
TTP160N03GT	TO-220	160N03GT

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted			
Barantar	Cumple of	Value	11-11
Parameter	Symbol	TO-252, TO-220	- Unit
Drain-Source Voltage ($V_{GS} = 0V$)	V _{DSS}	30	V
Continuous Drain Current	Ι _D	160	A
Pulsed Drain Current (note1)	I _{DM}	640	A
Gate-Source Voltage	V _{GSS}	±20	V
Single Pulse Avalanche Energy (note2)	E _{AS}	277	mJ
Avalanche Current	I _{As}	43	A
Power Dissipation ($T_c = 25^{\circ}C$)	P _D	143	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+175	°C

Thermal Resistance			
Peremeter	Complete	Value	Unit
Parameter	Symbol	TO-252, TO-220	
Thermal Resistance, Junction-to-Case	R _{thJC}	1.05	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	60	K/W



Specifications T _J = 25°C, ur	less othe	rwise noted	-			
Parameter	Symbol	Test One little	Value			1114
		Test Conditions	Min.	Тур.	Max.	Unit
Static		•				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	30			V
Zeus Cata Valtaria Drain Currant		V _{DS} = 30V, V _{GS} = 0V, T _J = 25°C			1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V, T _J = 125°C			100	μA 0
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 20V$			±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	1.7	2.4	V
	P	V _{GS} = 10V, I _D = 20A		1.6	2.1	mΩ
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 4.5V, I _D = 20A		2.1	3.0	mΩ
Forward Transconductance (Note3)	g _{fs}	V _{DS} = 10V, I _D = 20A		42.6		S
Dynamic		•				
Input Capacitance	C _{iss}	$\lambda = 0 \lambda$		9300		pF
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$		904		
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		813		
Total Gate Charge	Q _g			160		nC
Gate-Source Charge	Q _{gs}	$V_{DD} = 15V, I_{D} = 30A, V_{GS} = 10V$		18		
Gate-Drain Charge	Q_{gd}			34		
Turn-on Delay Time	t _{d(on)}			27		
Turn-on Rise Time	t _r	V _{DD} = 20V, I _D = 30A,		25		
Turn-off Delay Time	t _{d(off)}	$R_{\rm G} = 3\Omega$		90		ns
Turn-off Fall Time	t _f			40		
Drain-Source Body Diode Characteris	stics					
Continuous Body Diode Current	۱ _s	T _C = 25⁰C			160	٨
Pulsed Diode Forward Current	I _{SM}				640	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 30A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 30A,		43		ns
Reverse Recovery Charge	Q _{rr}	di _F /dt = 100A/µs		40		nC

Notes

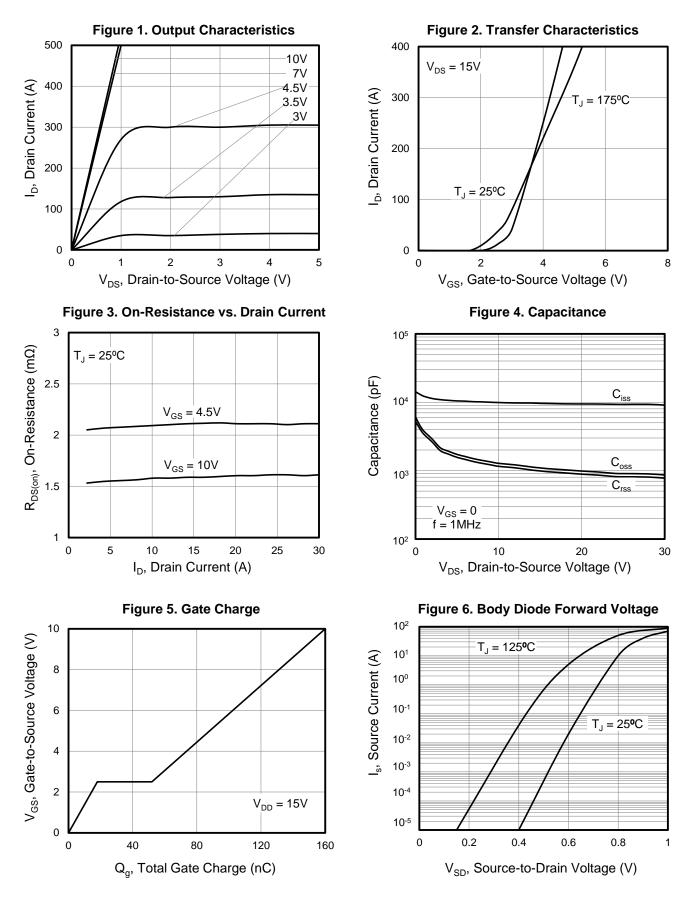
- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2. I_{AS} = 43A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 1%



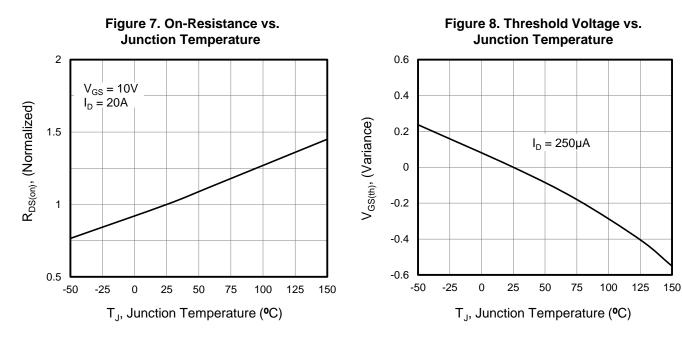
TTD160N03GT, TTP160N03GT

Wuxi Unigroup Microelectronics Company

Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

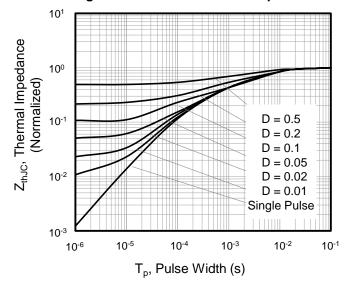


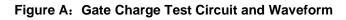


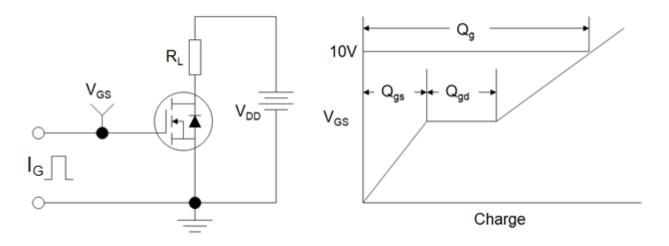


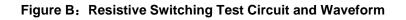
Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted











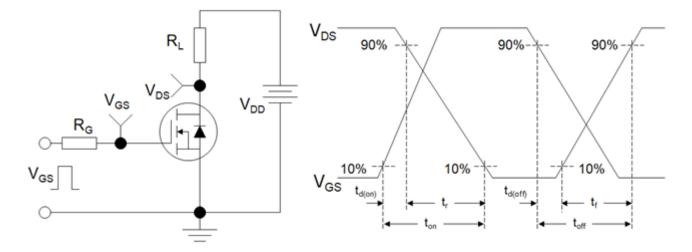
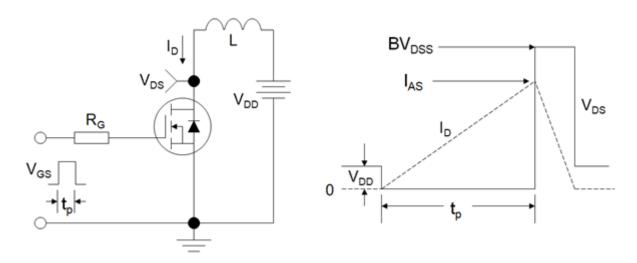
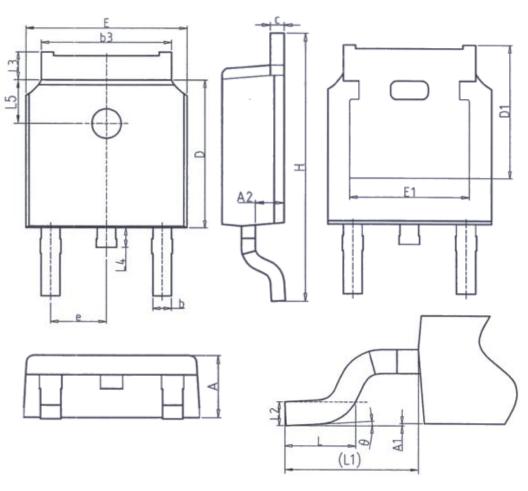


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





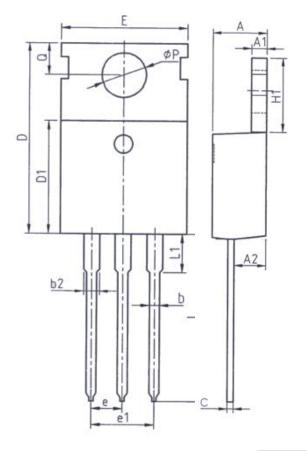
TO-252

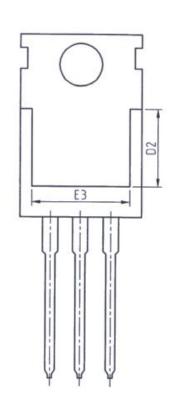


Unit: mm			
Symbol	Min.	Max.	
Α	2.20	2.40	
A1	0.00	0.20	
A2	0.97	1.17	
b	0.68	0.90	
b3	5.20	5.50	
с	0.43	0.63	
D	5.98	6. 22	
D1	D1 5. 30REF		
E	6.40	6.80	
E1	4.63	-	

Unit: mm			
Symbol	Min.	Max.	
e	2. 286BSC		
H	9.40	10.50	
L	1.38	1.75	
L1	2. 90REF		
L2	0. 51BSC		
L3	0.88	1.28	
L4	_	1.00	
L5	1.65	1.95	
θ	0°	8°	

TO-220





Unit: mm		
Symbol	Min.	Max.
Α	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
С	0.40	0.65
D	15. 10	16. 10
D1	8.80	9.40
D2	5.50	-

Unit: mm			
Symbol	Min.	Max.	
E	9.70	10. 30	
E3	7.00	-	
e	2. 54BSC		
e1	5. 08BSC		
H1	6. 25	6.85	
L	12.75	13.80	
L1	_	3. 40	
Ρ	3. 40	3.80	
Q	2.60	3.00	



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